

**Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
100V	6Ω @ V <sub>GS</sub> = 10V	230mA
	10Ω @ V <sub>GS</sub> = 4.5V	178mA

**Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

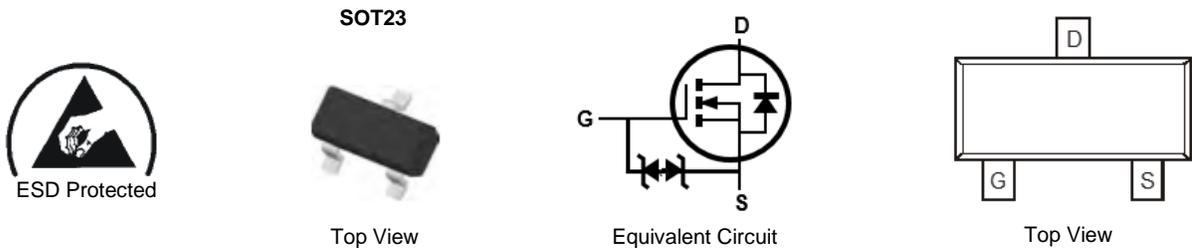
- Small Servo Motor Control
- Power MOSFET Gate Drivers
- Switching Applications

**Features and Benefits**

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- High Drain-Source Voltage Rating
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.**

**Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (E3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

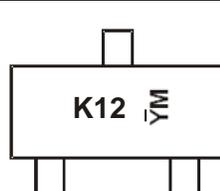


**Ordering Information** (Note 4)

Part Number	Case	Packaging
BSS123K-7	SOT23	3,000/Tape & Reel
BSS123K-13	SOT23	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**



K12 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: H = 2020)  
 M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	H	I	J	K	L	M	N	O	P	R	S	T

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic				Symbol	Value	Unit
Drain-Source Voltage				V <sub>DSS</sub>	100	V
Gate-Source Voltage				V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6)	V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	230 184	mA
Maximum Body Diode Forward Current				I <sub>S</sub>	230	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)				I <sub>DM</sub>	600	mA
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)				I <sub>SM</sub>	600	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P <sub>D</sub>	0.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R <sub>θJA</sub>	264	°C/W
Total Power Dissipation (Note 6)			P <sub>D</sub>	0.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R <sub>θJA</sub>	178	°C/W
Operating and Storage Temperature Range			T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0	µA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	µA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.8	—	2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	3.6 3.8	6 10	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.17A V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 0.17A
Diode Forward Voltage	V <sub>SD</sub>	—	0.87	1.3	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 0.34A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>ISS</sub>	—	38	—	pF	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>OSS</sub>	—	2.9	—	pF	
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	1.8	—	pF	
Gate Resistance	R <sub>g</sub>	—	37	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	0.7	—	nC	V <sub>DS</sub> = 50V, I <sub>D</sub> = 0.23A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	1.3	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	0.2	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	0.4	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	2.9	—	ns	
Turn-On Rise Time	t <sub>r</sub>	—	2.4	—	ns	V <sub>DD</sub> = 50V, V <sub>GS</sub> = 10V, R <sub>g</sub> = 50Ω, I <sub>D</sub> = 0.23A
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	15.3	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	6.7	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

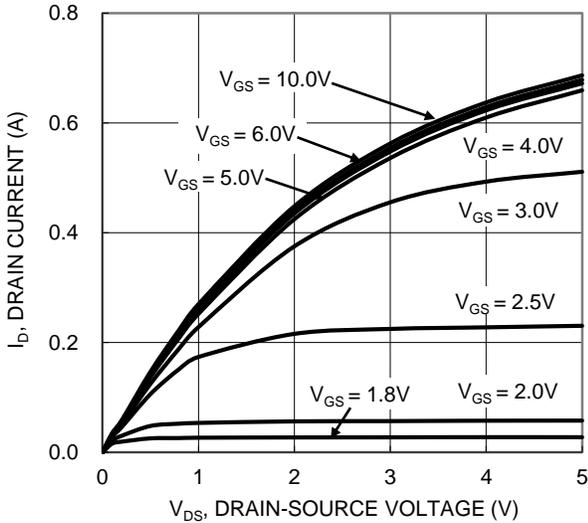


Figure 1. Typical Output Characteristic

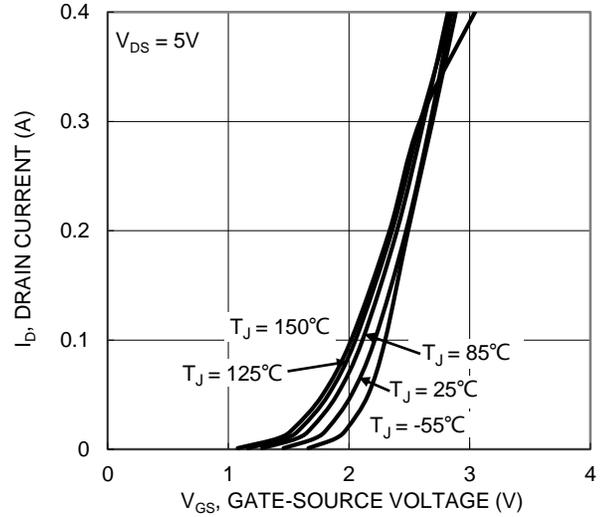


Figure 2. Typical Transfer Characteristic

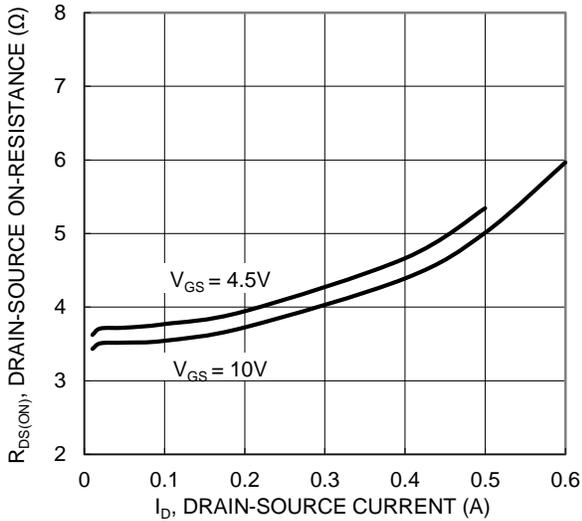


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

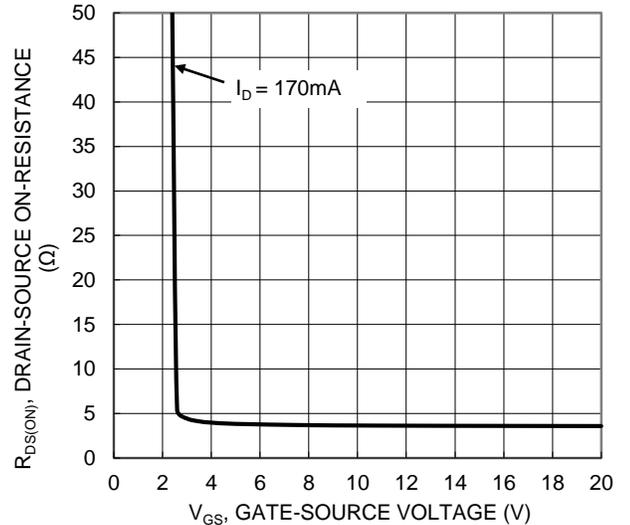


Figure 4. Typical Transfer Characteristic

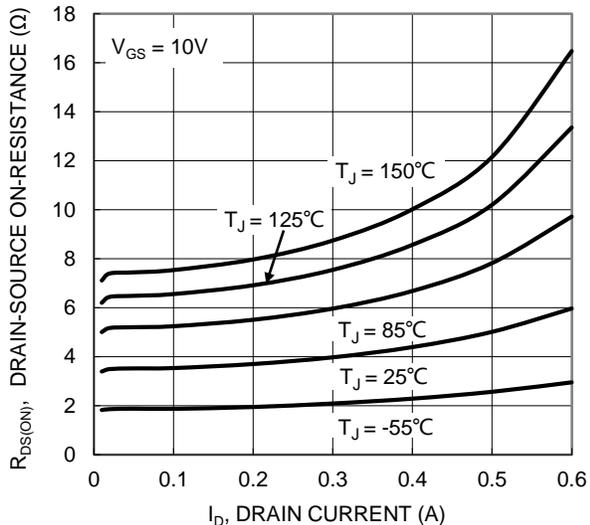


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

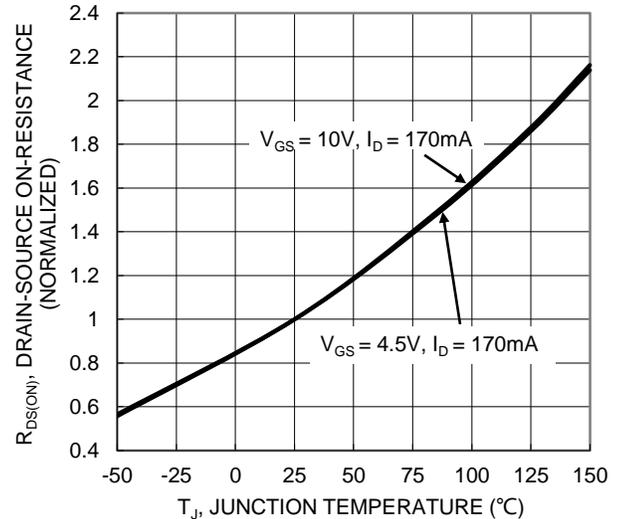


Figure 6. On-Resistance Variation with Junction Temperature

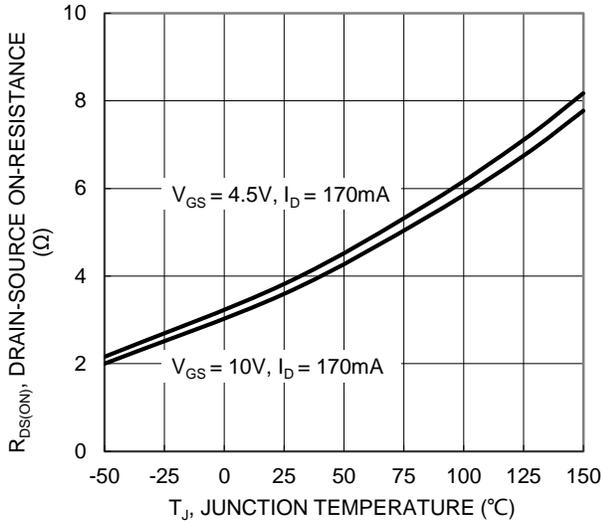


Figure 7. On-Resistance Variation with Junction Temperature

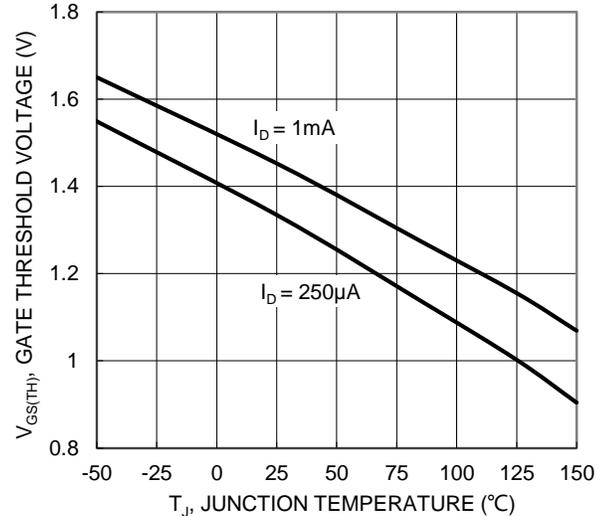


Figure 8. Gate Threshold Variation vs. Junction Temperature

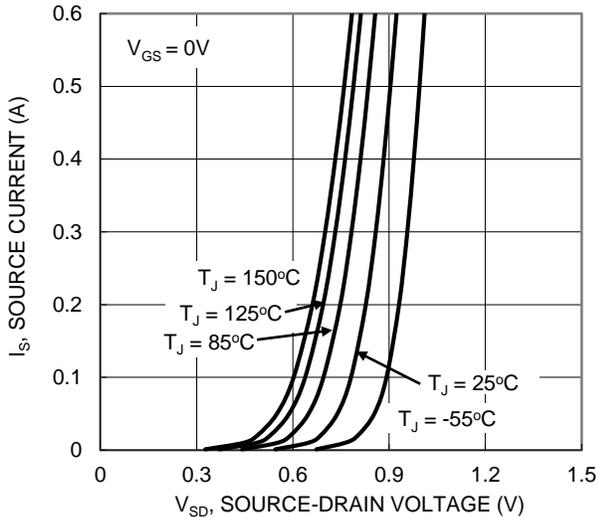


Figure 9. Diode Forward Voltage vs. Current

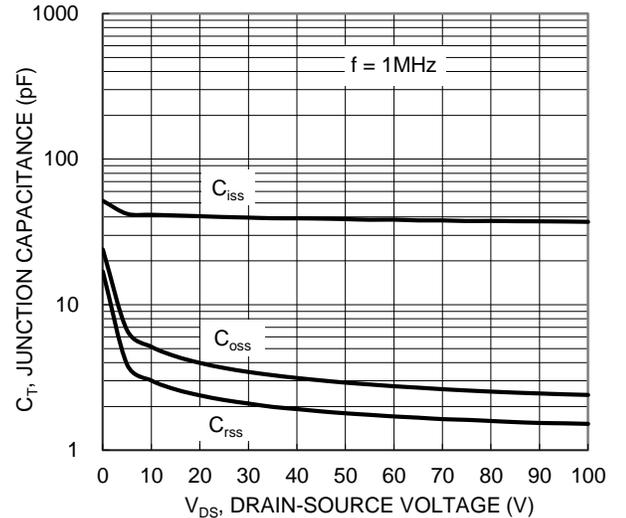


Figure 10. Typical Junction Capacitance

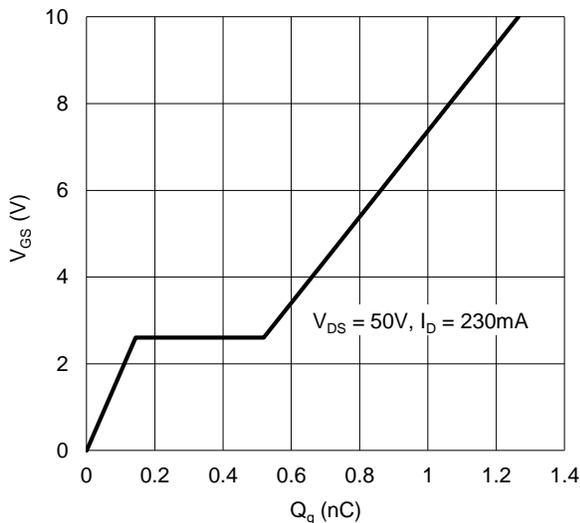


Figure 11. Gate Charge

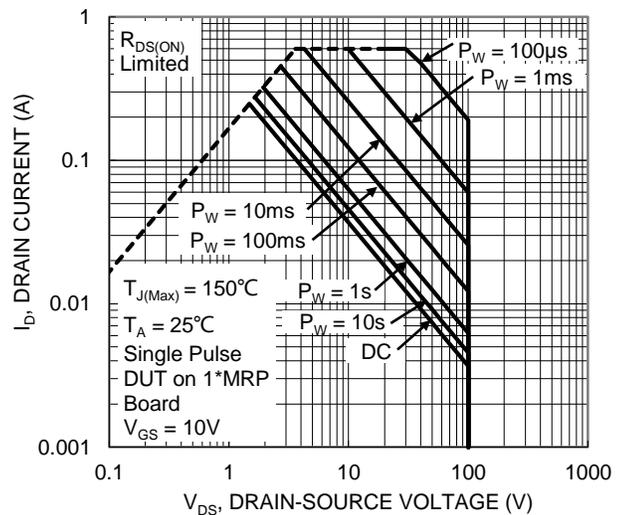


Figure 12. SOA, Safe Operation Area

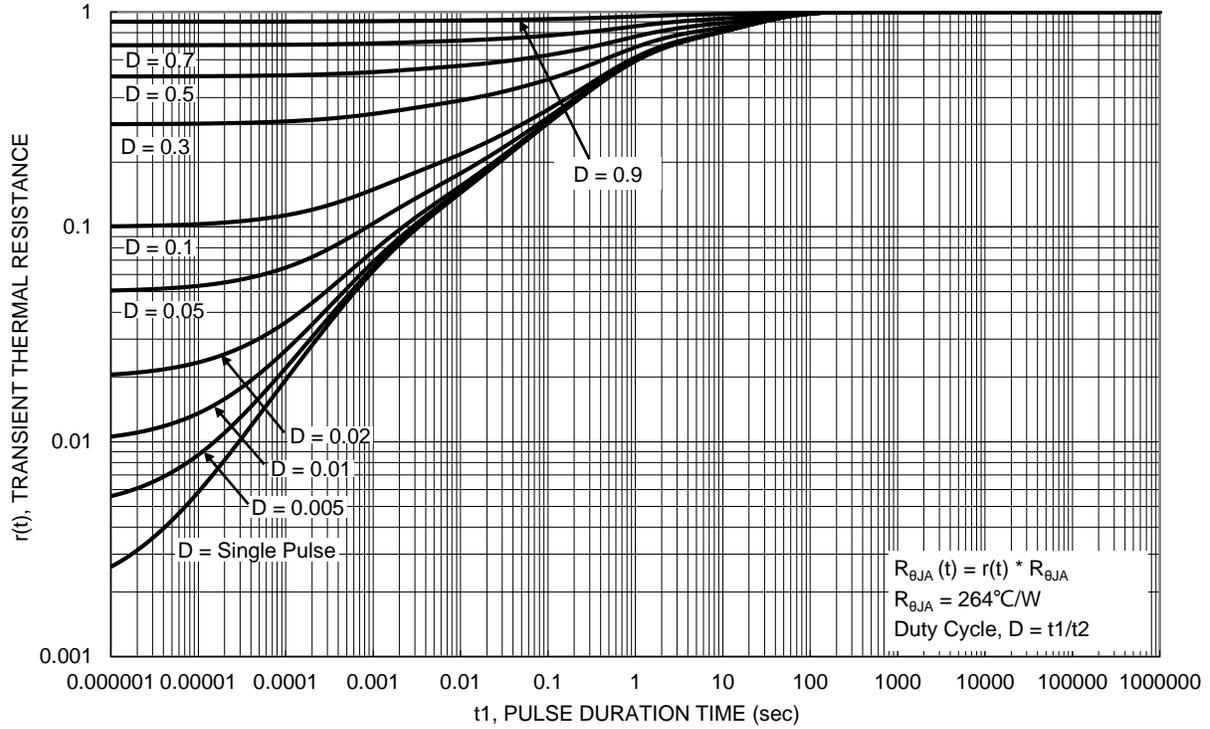
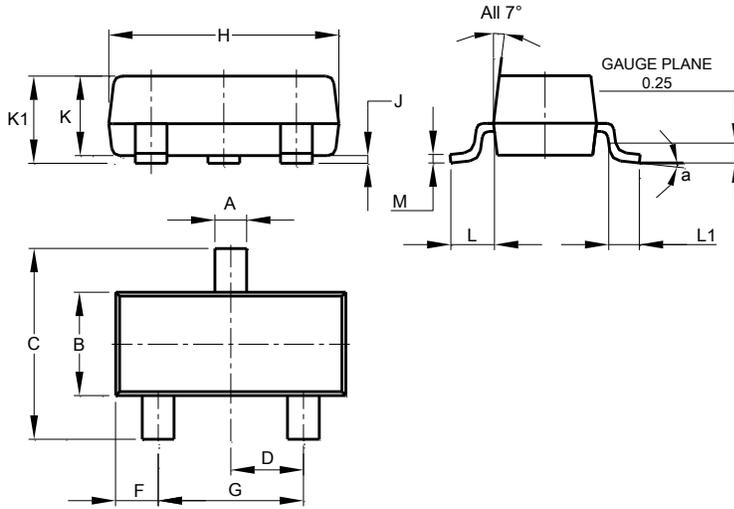


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23**

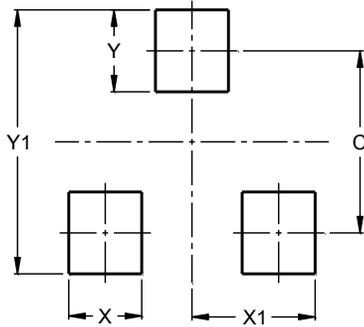


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23**



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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